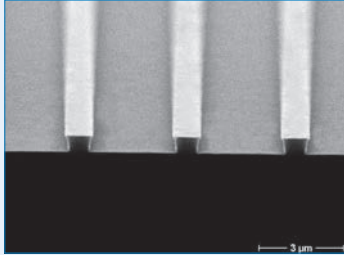


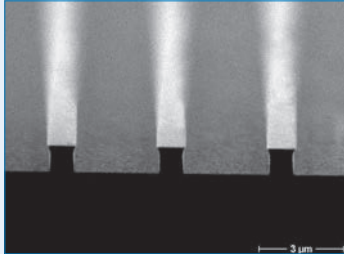
ma-P 1200 — Positive Tone Photoresist Series

Resists for UV Lithography

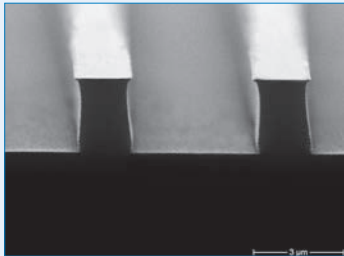
Resist patterning with mask aligner, broadband exposure



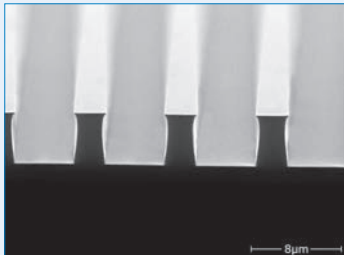
0.5 μm ma-P 1205, 1 μm lines, 3 μm spaces



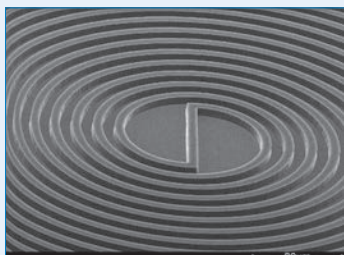
1 μm ma-P 1210, 1 μm lines, 3 μm spaces



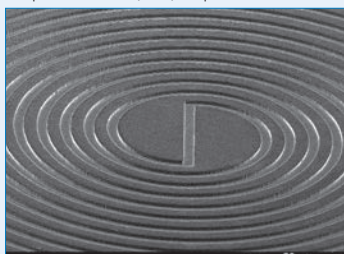
2.5 μm ma-P 1225, 2 μm lines, 4 μm spaces



4 μm ma-P 1240, 3 μm lines, 5 μm spaces



7.5 μm ma-P 1275, coil, 10 turns



5 μm electroplated Ni coil, 10 μm turns

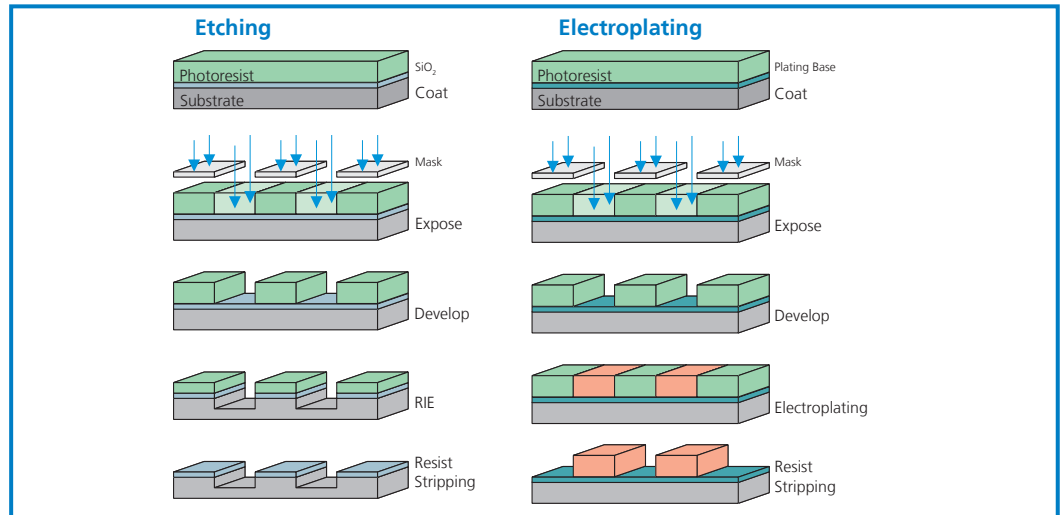
Unique features

- High pattern stability in wet etch processes and acid and alkaline plating baths
- Highly stable in dry etch processes e.g. CHF_3 , CF_4 , SF_6
- Aqueous alkaline development
- Easy to remove
- Resists available in a variety of viscosities

Applications

- Mask for etching e.g.
 - Si, SiO_2
 - Metals
 - Semiconductors
- Mask for ion implantation
- Mould for electroplating

Process flow



Technical data

Resist		ma-P 1205	ma-P 1210	ma-P 1215	ma-P 1225	ma-P 1240	ma-P 1275
Film thickness	μm	0.5	1.0	1.5	2.5	4.0	7.5
Spin coating	rpm s	3000 30					
Spectral sensitivity		broadband, g-, h-, i-line					
Dose @ 365 nm (broadband exposure)	mJ cm ⁻²	35	35	45	55	110	150

